Buried Oxide 400nm
- a-Si dep. 40nm and SPC 600 °C, 24hrs
- BF₂ doping, 2x14 cm⁻²
- Raised S/D pad patterning
- a-Si dep. 40nm, SPC and BF₂ doping
- Active patterning
- Oxide trimming
- Gate-oxide growth 20nm and N⁺ gate
- Gate patterning
- Passivation and Metallization
- H₂ sintering, 400 °C/30min